



PSMN4R2-80YSE

N-channel 80 V, 4.2 mOhm MOSFET with enhanced SOA in LFAK56E

3 September 2021

Product data sheet

1. General description

N-channel enhancement mode MOSFET in a LFAK56E package qualified to 175 °C. Part of Nexperia's "ASFETs for hotswap" portfolio, the PSMN4R2-80YSE delivers very low R_{DSon} and a very strong linear-mode (SOA) performance in a high-reliability copper-clip LFAK56E package.

PSMN4R2-80YSE complements the latest "hot-swap" controllers – robust enough to withstand substantial inrush currents during turn-on, low R_{DSon} to minimize I^2R losses delivering optimum efficiency when turned fully ON and an 80% smaller footprint than existing D2PAK types.

2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Low R_{DSon} for low I^2R conduction losses
- LFAK56E package for applications that demand the highest performance and reliability in a 30 mm² footprint

3. Applications

- Hot swap
- Load switch
- Soft start
- E-fuse
- Telecommunication systems based on a 48 V backplane/supply rail

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---|-----|-----|-----|------|
| V_{DS} | drain-source voltage | $25\text{ °C} \leq T_j \leq 175\text{ °C}$ | - | - | 80 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ Fig. 2 | - | - | 170 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C};$ Fig. 1 | - | - | 294 | W |
| T_j | junction temperature | | -55 | - | 175 | °C |
| Static characteristics | | | | | | |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ Fig. 12 | - | 3.2 | 4.2 | mΩ |
| | | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 100\text{ °C};$ Fig. 13 | - | 4.6 | 6.4 | mΩ |
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $I_D = 25\text{ A}; V_{DS} = 40\text{ V}; V_{GS} = 10\text{ V};$ $T_j = 25\text{ °C};$ Fig. 14 ; Fig. 15 | 3 | 11 | 26 | nC |
| $Q_{G(tot)}$ | total gate charge | | 37 | 73 | 110 | nC |

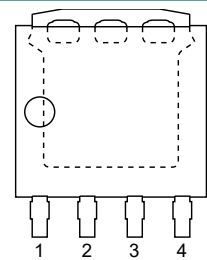
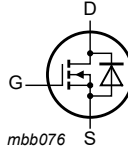
N-channel 80 V, 4.2 mOhm MOSFET with enhanced SOA in LPAK56E

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------------------|--|--|-----|-----|-----|--------|
| Avalanche ruggedness | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 57\text{ A}$; $V_{sup} \leq 80\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; unclamped; $t_p = 126\ \mu\text{s}$; Fig. 4 | [1] | - | - | 374 mJ |
| Source-drain diode | | | | | | |
| Q_r | recovered charge | $I_S = 25\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 40\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 18 | - | 35 | - | nC |

[1] Protected by 100% test

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|---|
| 1 | S | source |  <p>LPAK56E; Power-SO8 (SOT1023)</p> |  <p>mbb076</p> |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | Version |
|---------------|--------------------|--|---------|
| | Name | Description | |
| PSMN4R2-80YSE | LPAK56E; Power-SO8 | plastic, single-ended surface-mounted package (LPAK56); 4 leads; 1.27 mm pitch | SOT1023 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|---------------|--------------|
| PSMN4R2-80YSE | 4E2S80J |

8. Limiting values

Table 5. Limiting values

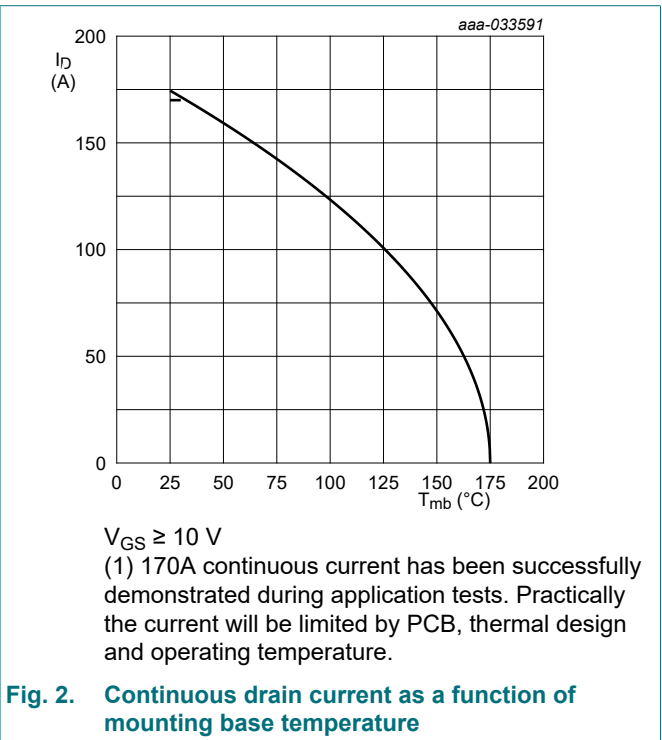
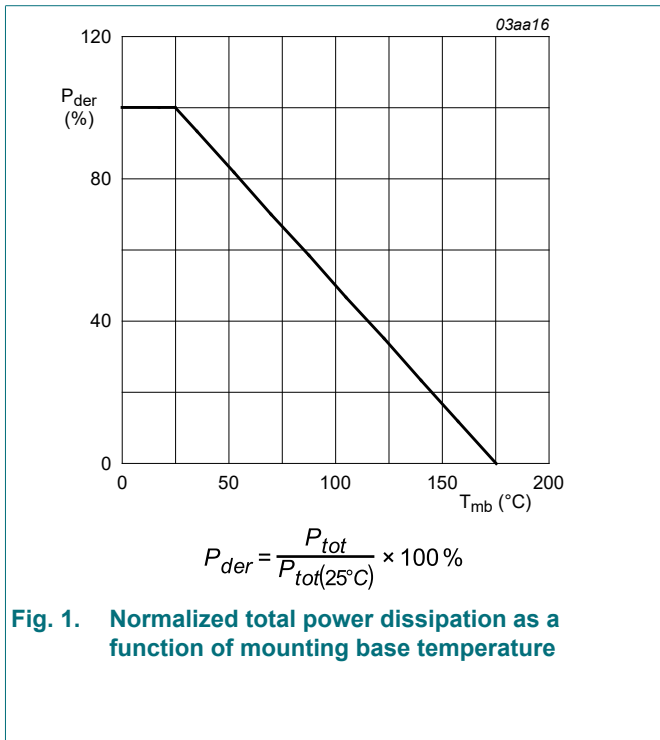
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|---|-----|-----|------|
| V_{DS} | drain-source voltage | $25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$ | - | 80 | V |
| V_{DGR} | drain-gate voltage | $25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$; $R_{GS} = 20\text{ k}\Omega$ | - | 80 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 1 | - | 294 | W |

N-channel 80 V, 4.2 mOhm MOSFET with enhanced SOA in LPAK56E

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------------------|--|--|-----|-----|--------|
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2 | - | 170 | A |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; Fig. 2 | - | 123 | A |
| I _{DM} | peak drain current | pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; Fig. 3 | - | 698 | A |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| T _j | junction temperature | | -55 | 175 | °C |
| T _{slid(M)} | peak soldering temperature | | - | 260 | °C |
| Source-drain diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 170 | A |
| I _{SM} | peak source current | pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C | - | 698 | A |
| Avalanche ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I _D = 57 A; V _{sup} ≤ 80 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; t _p = 126 μs; Fig. 4 | [1] | - | 374 mJ |
| I _{AS} | non-repetitive avalanche current | V _{sup} = 80 V; V _{GS} = 10 V; T _{j(init)} = 25 °C; R _{GS} = 50 Ω | [1] | - | 57 A |

[1] Protected by 100% test



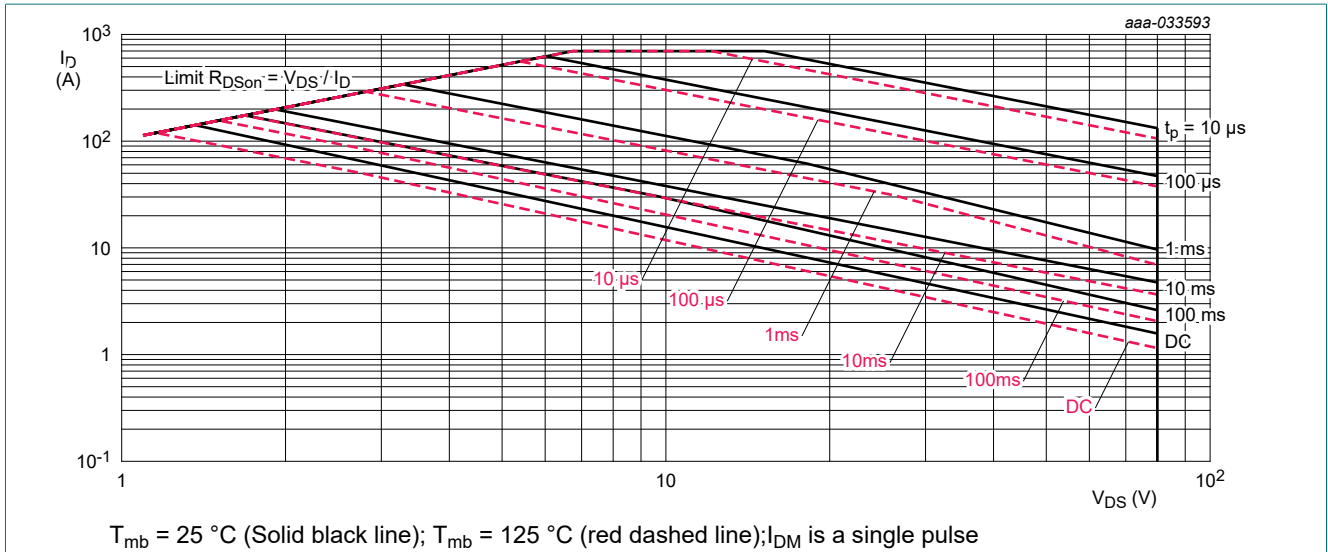


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

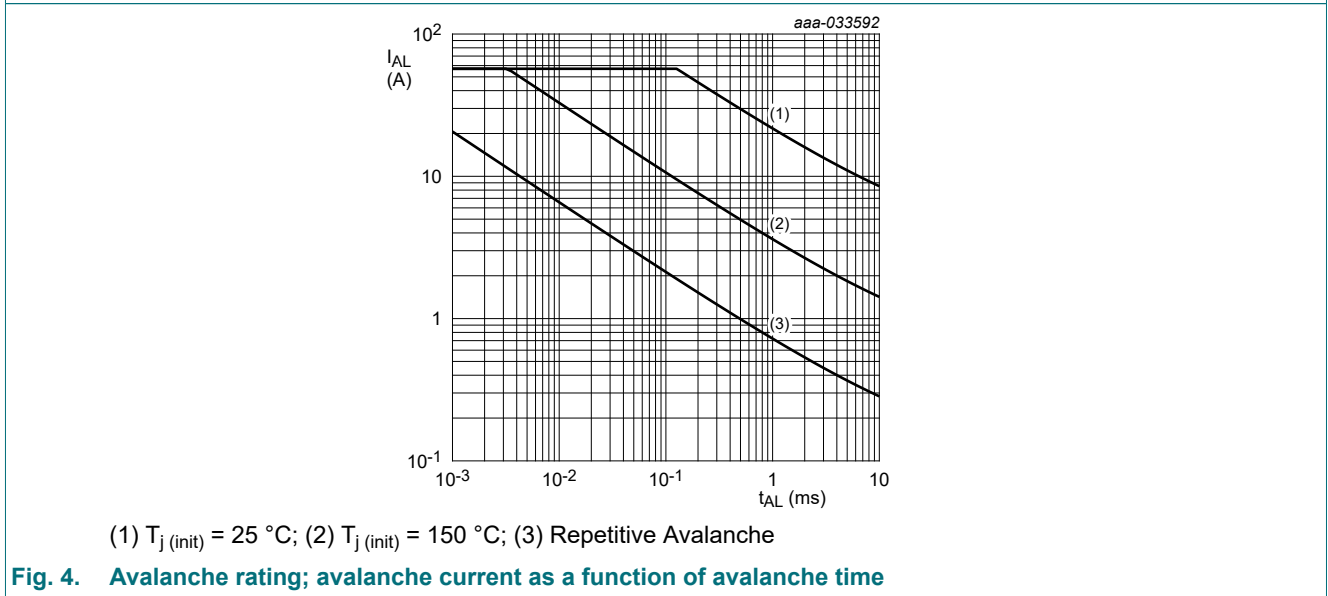


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5 | - | 0.45 | 0.51 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Fig. 6 | - | 42 | - | K/W |
| | | Fig. 7 | - | 85 | - | K/W |

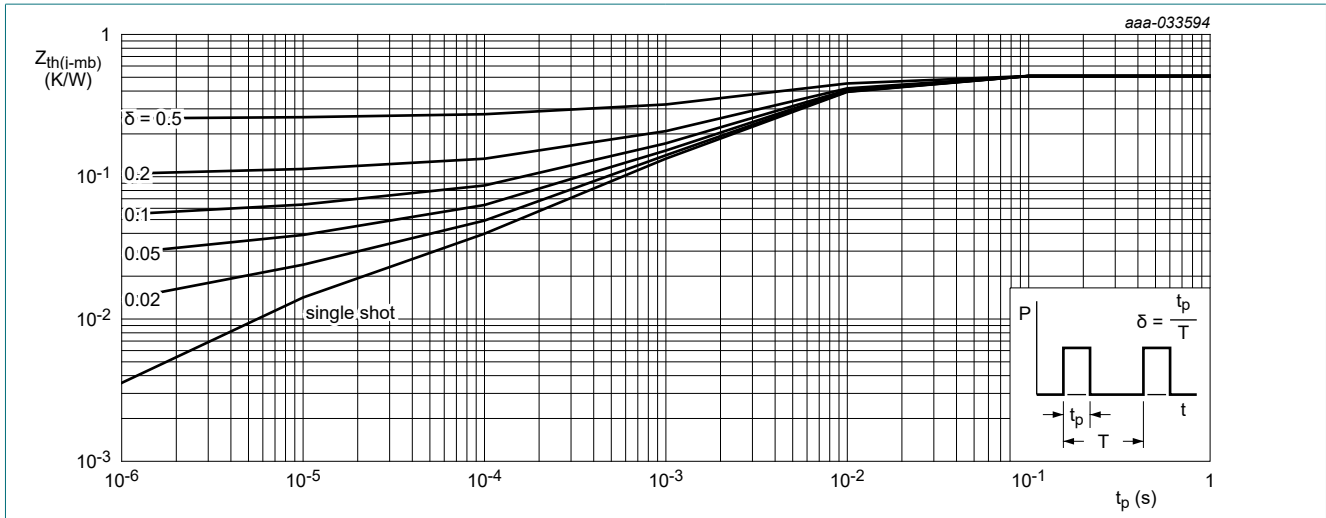


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

aaa-027933

Copper area 25.4 mm square; 70 μm thick on FR4 board

aaa-027935

70 μm thick copper on FR4 board

Fig. 6. PCB layout for thermal resistance from junction to ambient

Fig. 7. PCB layout with minimum footprint for thermal resistance from junction to ambient

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|--|---|-----|------|-----|------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$ | 80 | - | - | V |
| | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$ | 72 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C; \text{ Fig. 11}$ | 2 | 2.6 | 3.6 | V |
| | | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$ | - | 1.6 | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$ | - | 3 | - | V |
| $\Delta V_{GS(th)}/\Delta T$ | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$ | - | -6.1 | - | mV/K |
| I_{DSS} | drain leakage current | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 0.02 | 1 | μA |
| | | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$ | - | 5.5 | 100 | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 2 | 100 | nA |
| | | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 2 | 100 | nA |

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| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-----------------------------------|---|------|------|------|------------|
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_J = 25\text{ }^\circ\text{C};$ Fig. 12 | - | 3.2 | 4.2 | m Ω |
| | | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_J = 100\text{ }^\circ\text{C};$ Fig. 13 | - | 4.6 | 6.4 | m Ω |
| | | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_J = 175\text{ }^\circ\text{C};$ Fig. 13 | - | 6.3 | 9.3 | m Ω |
| R_G | gate resistance | $f = 1\text{ MHz}; T_J = 25\text{ }^\circ\text{C}$ | 0.52 | 1.04 | 2.08 | Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 25\text{ A}; V_{DS} = 40\text{ V}; V_{GS} = 10\text{ V};$ $T_J = 25\text{ }^\circ\text{C};$ Fig. 14; Fig. 15 | 37 | 73 | 110 | nC |
| | | $I_D = 0\text{ A}; V_{DS} = 0\text{ V}; V_{GS} = 10\text{ V};$ $T_J = 25\text{ }^\circ\text{C}$ | - | 40 | - | nC |
| Q_{GS} | gate-source charge | $I_D = 25\text{ A}; V_{DS} = 40\text{ V}; V_{GS} = 10\text{ V};$ $T_J = 25\text{ }^\circ\text{C};$ Fig. 14; Fig. 15 | 18 | 31 | 43 | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | | - | 16.2 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | - | 14.8 | - | nC |
| Q_{GD} | gate-drain charge | | 3 | 11 | 26 | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D = 25\text{ A}; V_{DS} = 40\text{ V}; T_J = 25\text{ }^\circ\text{C};$ Fig. 14; Fig. 15 | - | 5.6 | - | V |
| C_{iss} | input capacitance | $V_{DS} = 40\text{ V}; V_{GS} = 0\text{ V}; f = 0.5\text{ MHz};$ $T_J = 25\text{ }^\circ\text{C};$ Fig. 16 | 3429 | 5714 | 8000 | pF |
| C_{oss} | output capacitance | | 893 | 1488 | 2381 | pF |
| C_{rss} | reverse transfer capacitance | | 5 | 55 | 164 | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 40\text{ V}; R_L = 1.6\text{ }^\Omega; V_{GS} = 10\text{ V};$ $R_{G(ext)} = 5\text{ }^\Omega; T_J = 25\text{ }^\circ\text{C}$ | - | 23 | - | ns |
| t_r | rise time | | - | 25 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 32 | - | ns |
| t_f | fall time | | - | 24 | - | ns |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_J = 25\text{ }^\circ\text{C};$ Fig. 17 | - | 0.81 | 1 | V |
| t_{rr} | reverse recovery time | $I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 40\text{ V}; T_J = 25\text{ }^\circ\text{C};$ Fig. 18 | - | 38 | - | ns |
| Q_r | recovered charge | | - | 35 | - | nC |

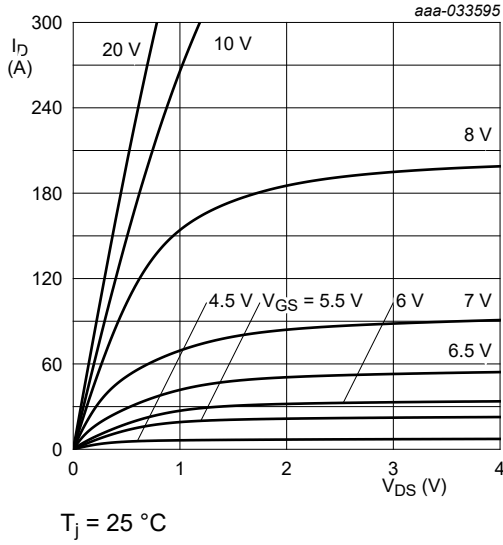


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

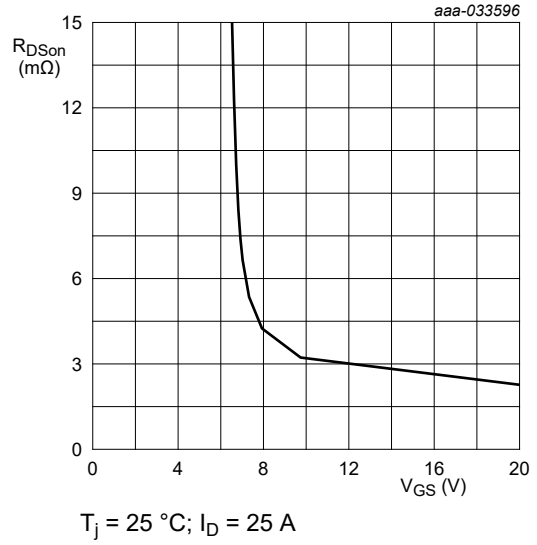


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

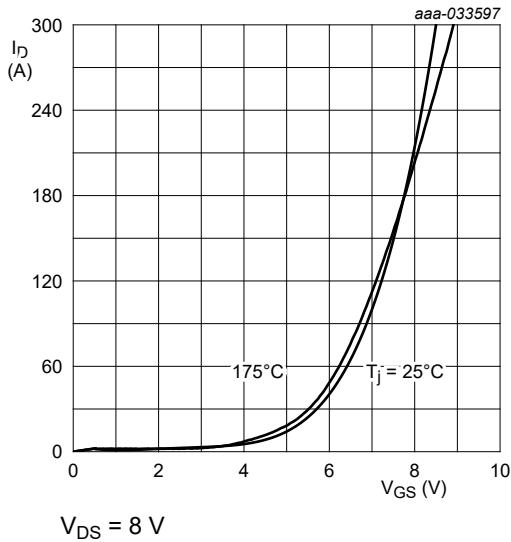


Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values

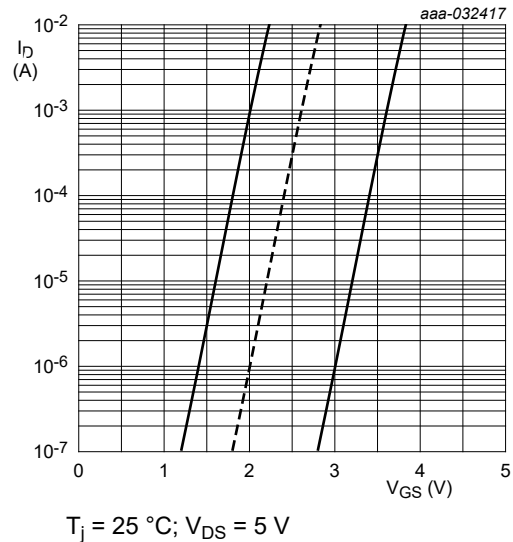


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

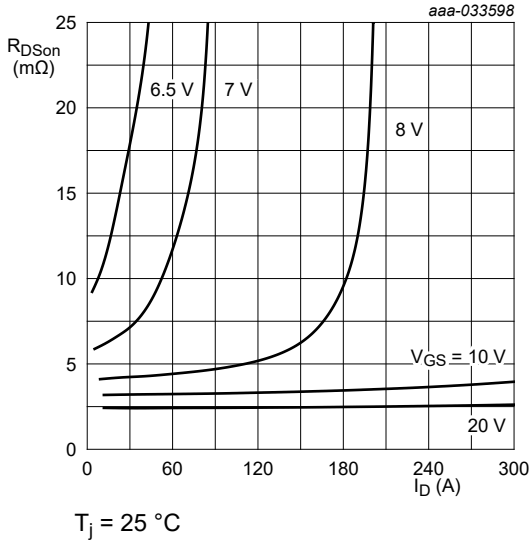
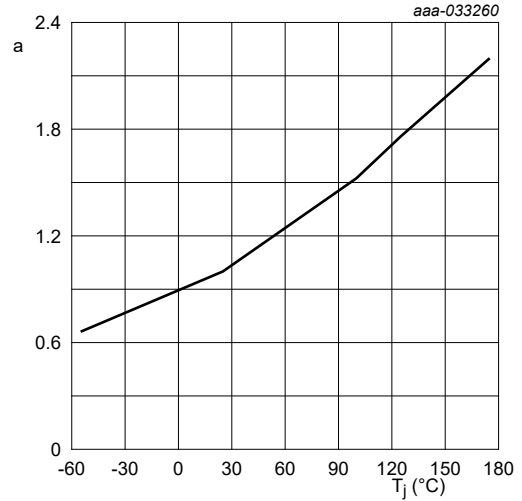


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^\circ\text{C})}$$

Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

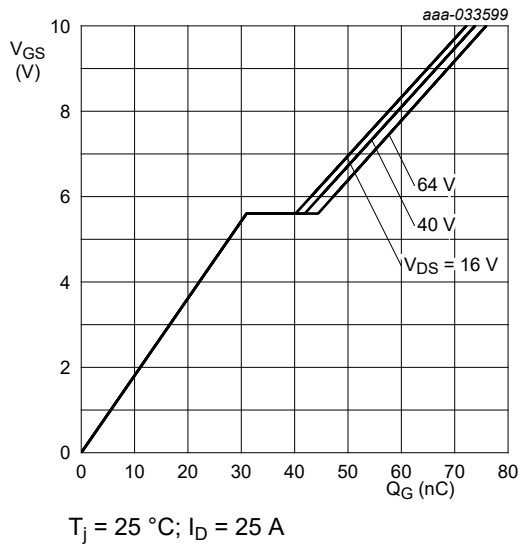


Fig. 14. Gate-source voltage as a function of gate charge; typical values

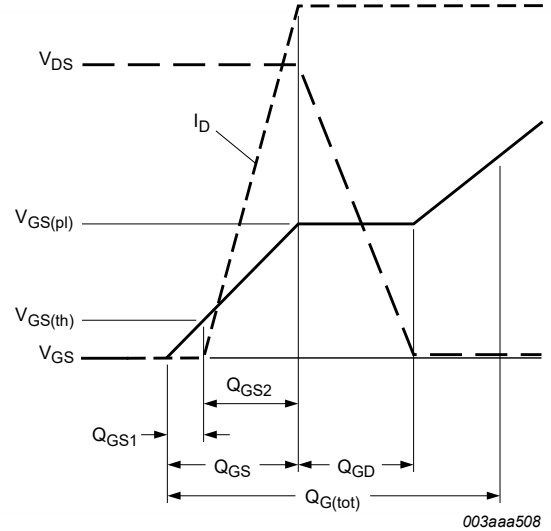


Fig. 15. Gate charge waveform definitions

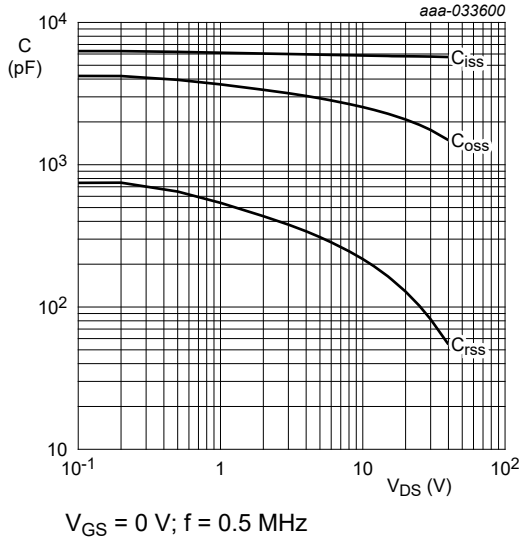


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

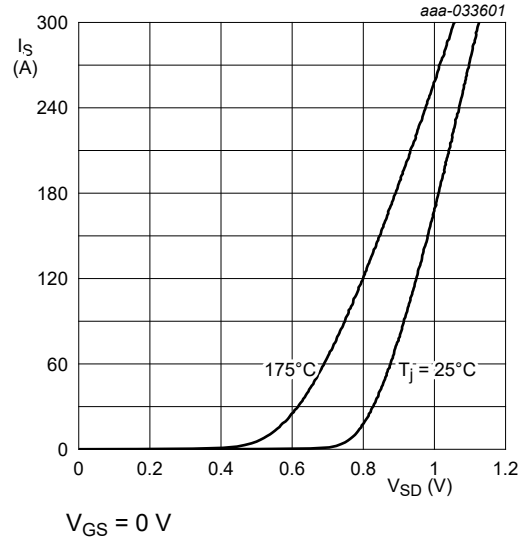


Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

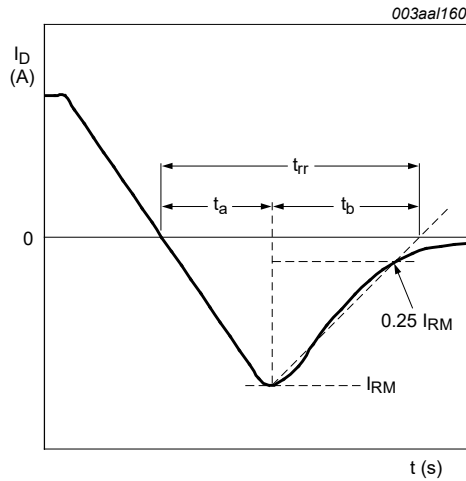


Fig. 18. Reverse recovery timing definition

11. Package outline

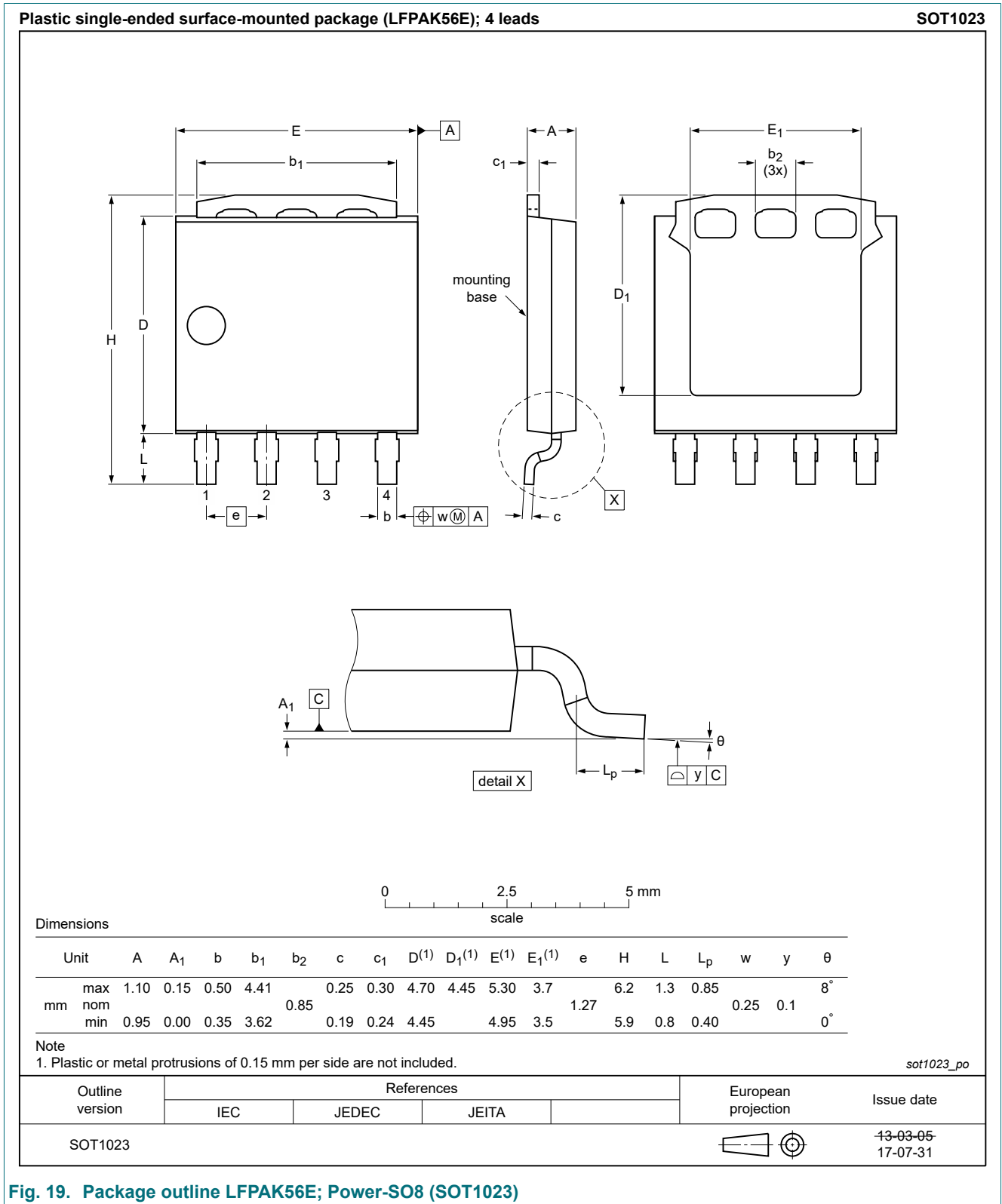


Fig. 19. Package outline LPAK56E; Power-SO8 (SOT1023)

12. Soldering

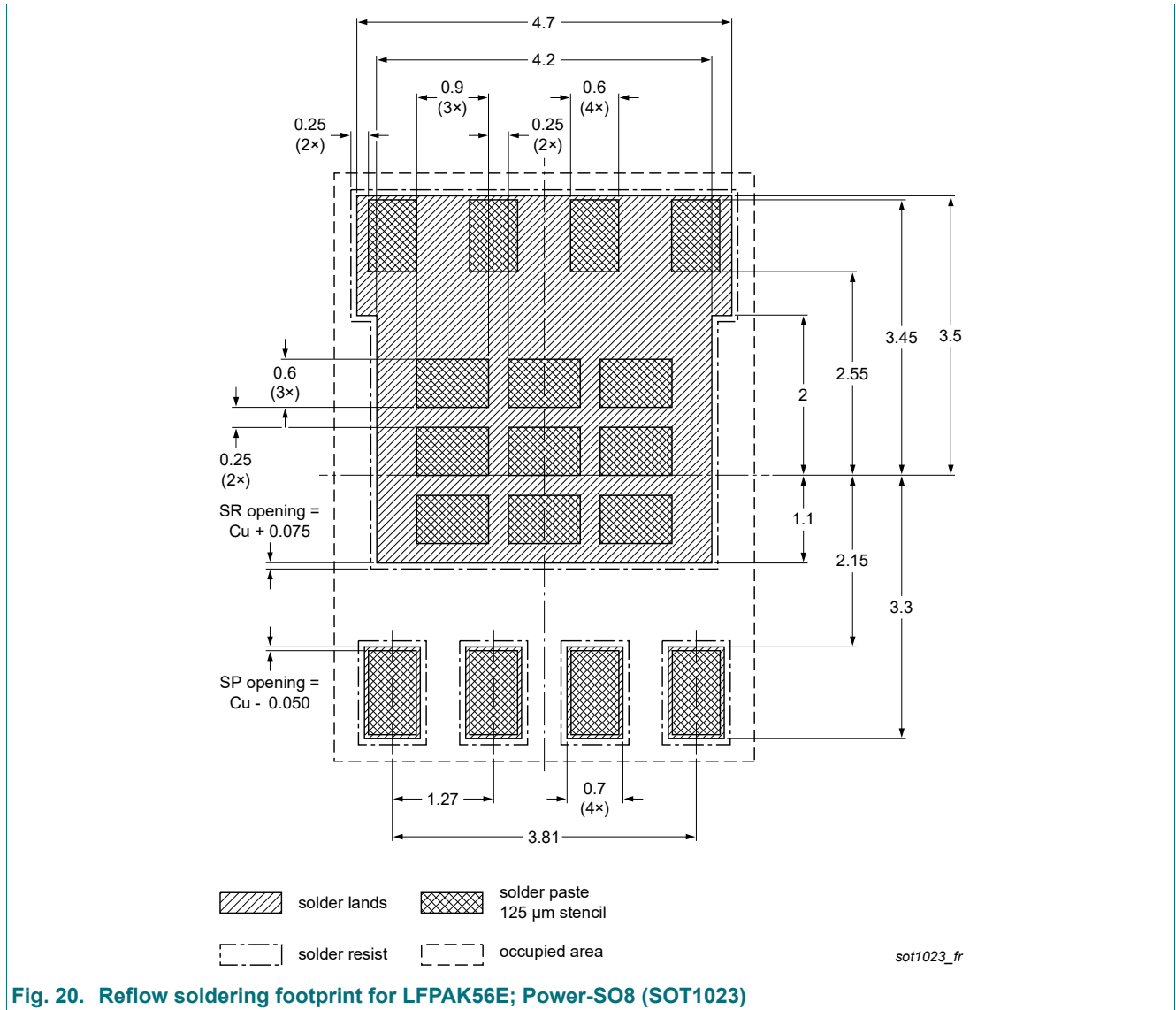


Fig. 20. Reflow soldering footprint for LPAK56E; Power-SO8 (SOT1023)

13. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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